

Description

The DMG9926UDM uses advanced trench technology to provide excellent $R_{\text{DS}(\text{ON})}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.



General Features

 $V_{DS} = 20V, I_{D} = 6A$

 $R_{DS(ON)}$ <25m Ω @ V_{GS} =4.5V

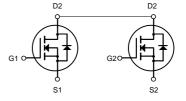


Application

Battery protection

Load switch

Power management



Dual N-Channel MOSFET

Package Marking and Ordering Information

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Product ID	Pack	Brand	Qty(PCS)
DMG9926UDM	SOT-23-6L	HXY MOSFET	3000

Absolute Maximum Ratings@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	20	V
V _G S	Gate-Source Voltage	<u>+</u> 10	V
I _D @T _A =25°C	Drain Current, V _{GS} @ 4.5V ³	6	Α
Ідм	Pulsed Drain Current ¹	25	А
P _D @T _A =25°C	Total Power Dissipation	1.25	W
Тѕтс	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C
Rthj-a	Maximum Thermal Resistance, Junction- ambient ³	100	°C/W



Electrical Characteristics (T_A=25℃ unless otherwise noted)

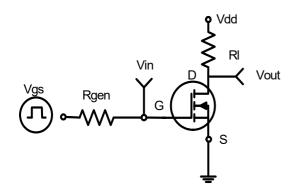
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	20	21	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =19.5V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±10V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)			•			
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS},I_{D}=250\mu A$	0.5	0.7	1.2	V
Danier Courses On Otata Basistanas	R _{DS(ON)}	V _{GS} =4.5V, I _D =4A	-	22	25	mΩ
Drain-Source On-State Resistance		V_{GS} =2.5V, I_D =3A	-	26	31	mΩ
Forward Transconductance	g FS	$V_{DS}=5V,I_{D}=4A$	-	10	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}		-	600	-	PF
Output Capacitance	C _{oss}	V_{DS} =8 V , V_{GS} =0 V , F=1.0MHz	-	330	-	PF
Reverse Transfer Capacitance	C _{rss}	F-1.UIVITZ	-	140	-	PF
Switching Characteristics (Note 4)			'			
Turn-on Delay Time	t _{d(on)}		-	18	-	nS
Turn-on Rise Time	t _r	V_{DD} =10 V , I_{D} =1 A	-	5	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =4 V , R_{GEN} =10 Ω	-	43	-	nS
Turn-Off Fall Time	t _f		-	20	-	nS
Total Gate Charge	Qg	\/ -40\/ -40	-	11	-	nC
Gate-Source Charge	Q _{gs}	$V_{DS}=10V,I_{D}=4A,$	-	2.3	-	nC
Gate-Drain Charge	Q _{gd}	V _{GS} =4.5V	-	2.5	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =2A	-	8.0	1.2	V
Diode Forward Current (Note 2)	Is		-	-	2	Α

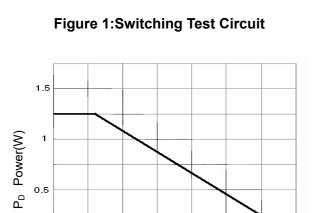
Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics





 T_J -Junction Temperature(°C) Figure 3 Power Dissipation

60

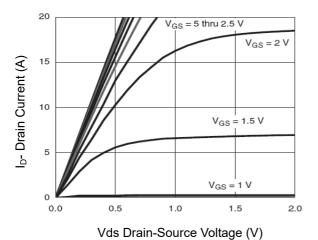


Figure 5 Output Characteristics

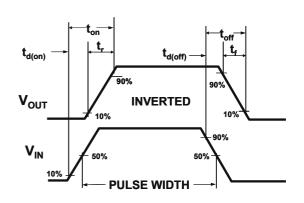


Figure 2:Switching Waveforms

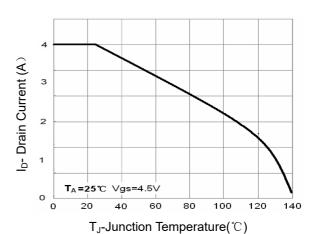


Figure 4 Drain Current

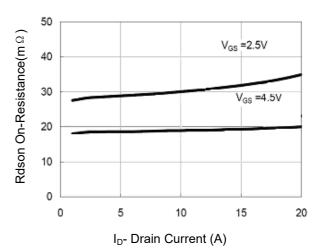


Figure 6 Drain-Source On-Resistance



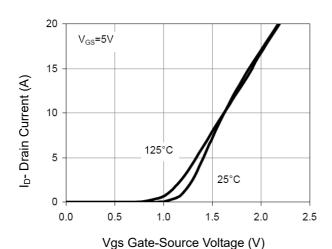


Figure 7 Transfer Characteristics

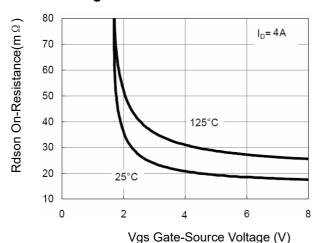
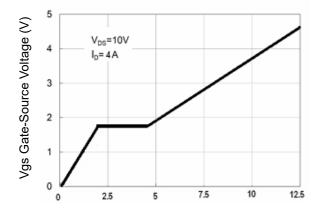
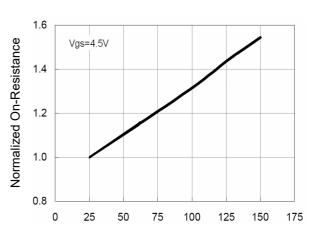


Figure 9 Rdson vs Vgs

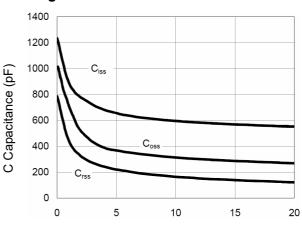


Qg Gate Charge (nC) Figure 11 Gate Charge

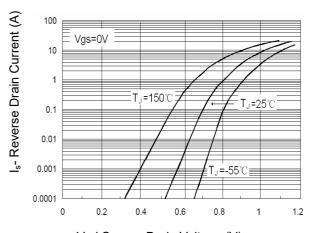


T_J-Junction Temperature(°C)

Figure 8 Drain-Source On-Resistance

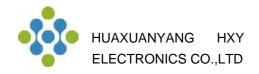


Vds Drain-Source Voltage (V)
Figure 10 Capacitance vs Vds



Vsd Source-Drain Voltage (V)

Figure 12 Source- Drain Diode Forward



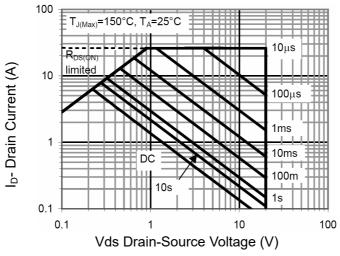


Figure 13 Safe Operation Area

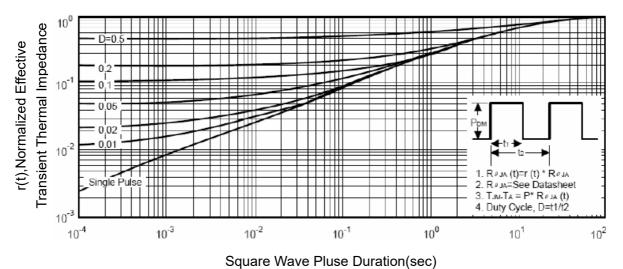
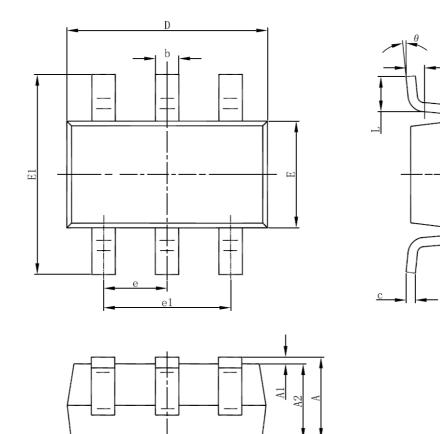


Figure 14 Normalized Maximum Transient Thermal Impedance



SOT-23-6L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	1.050	1.250	0.041	0.049	
A1	0.000	0.100	0.000	0.004	
A2	1.050	1.150	0.041	0.045	
b	0.300	0.500	0.012	0.020	
С	0.100	0.200	0.004	0.008	
D	2.820	3.020	0.111	0.119	
E	1.500	1.700	0.059	0.067	
E1	2.650	2.950	0.104	0.116	
е	0.950(BSC)		0.037(BSC)		
e1	1.800	2.000	0.071	0.079	
L	0.300	0.600	0.012	0.024	
θ	0°	8°	0°	8°	

Dual N-Channel Enhancement Mode MOSFET

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